

09/914044

ABSTRACT

The present invention provides an inspection object silicon wafer for the purpose of detecting crystal defects and the method of detection thereof, which make easy the detection of the number and location of the defects formed on the surface of the silicon wafer by performing heat treatment and epitaxial growth under a temperature condition in which the natural oxide film is removed but the state of the surface of the silicon wafer is preserved, specifically under a hydrogen atmosphere of normal pressure and a temperature between 900 °C and 1080 °C, through which defects having pits and projections are generated on the surface of the epitaxial layer, and by detecting the defects having pits and protrusions by a light scattering type particle inspection apparatus.

101121-44044